

India's Number 1 Education App

CHEMISTRY

BOOKS - NCERT CHEMISTRY (ENGLISH)

SOLID STATE

Multiple Choice Question Mcqs

1. which of the following favours the existence

of a substance in the solid state ?

a) High temperature

- b) Low temperature
- c) High thermal energy
- d) Weak cohesive forces
 - A. High temperature
 - B. Low temperature
 - C. high thermal enery
 - D. Weak cohesive forces

Answer: B

Watch Video Solution

2. which of the following is not a characteristic of a crystalline solid ? (a) Definite and characteristic heat of fusion. (b) Isotropic nature (c) A regular periodically repeated pattern of arrangement of constituent particles in the entire crystal. (d) A true solid.

A. Define and characterstic heat of fusion

B. Isotropic nature

C. A regular periodically repeated pattern

of arrangement of consituent particles

in the entire crystal

D. A true solid

Answer: B

Watch Video Solution

3. Which of the following is an amorphous solid? (1) Teflon (2) Cellophane (3) Poly vinyl chloride (4) Fibre glass (5) All of these

A. Graphite (C)

B. Quartz glass (SiO_2)

C. Chrome alum

D. Silicon carbide (SiC)

Answer: B



4. which of the following arrangements shows schematic alignment magnetic moments of antiferromagnetic substances?



 $\mathsf{B.} ~ {}^{\scriptscriptstyle (b)} \textcircled{} ~ \end{array}{} ~ \textcircled{} ~ \end{array}{} ~ \rule{} ~ \rule{}$

Answer: D

Watch Video Solution

5. which of the following is true about the value of refractive index of quartz glass ? a)
Same in all directions b) Different in all

directions c) Can not be measured d) Always

zero

A. Same in all directions

B. Different in different directions

C. Cannot be measured

D. Always zero

Answer: A

Watch Video Solution

6. Which of the following statement is not true about amorphous solids? (a) On heating, they may become crystalline at certain temperature. (b) They may become crystalline on keeping for long time. (c) Amorphous solids can be moulded by heating. (d) They are anisotropic in nature.

A. on heating they may become crystalline

at certain temperature

B. they may become crystlline on keeping

for long time

C. Amorphous solids can be moulded by

heating

D. they are aniotropic in a nature

Answer: D

Watch Video Solution

7. The sharp melting point of crystalline solids compared to amorphous solids is due to
a) a regular arrangement of constituent particles observed over a short distance in the

crystal lattice.

b) a regular arrangement of constituent
 particles observed over a long distance in the
 crystal lattice.

- c) Same arrangement of constituent particlesin different directions.
- d) Different arrangement of constituent particles in different directions.
 - A. a regular arrangement of constituent

partticles observed over a short distance

in the crystal lattice



Answer: B

Watch Video Solution

8. Iodine molecules are held in the crystal lattice by: a) London forces b) dipole-dipole interactions c) Covalent bonds d) Coulombic forces

A. London forces

- B. Dipole -dippole interactions
- C. Covvalent bonds
- D. Coulombic forces

Answer: A

Watch Video Solution

9. which of the following is a network solid? a) Sulphur dioxide (Solid) b) Iodine c) Diamond d) Ice

A. $SO_2(solid)$

- $\mathsf{B.}\,I_2$
- C. Diamond
- D. H_2O (ice)

Answer: C





10. which of the following solids is not an electrical conductor ?

(a) Mg(s) (b) TiO(s) (c) $I_2(s)$ (d) $H_2O(s)$

A. only 1

B. only 2

C. 3 and 4

D. 2,3 and 4

Answer: C





11. which of the following is not the characteristic of ionic solids?

A. Very low value of electrical conductivity

in the molten state

B. Brittle strong forces of interactions

C. Very strong forces of interactons

D. Anisotropic nature

Answer: A



12. Graphite is a good conductor of electricity

A. Lone pair of electrons

B. Free Valence electrons

C. Cations

D. anions

Answer: B





13. which of the following oxides behaves as conductor or insulator depending upon temperature ? (a)TiO $(b)SiO_2$ (c) TiO_3 (d) MgO A. TiO B. SiO_2

 $\mathsf{C}.\,TiO_3$

D. MgO

Answer: C



14. which of the following oxides shows electrical properties like metals ?

A. SiO_2

B. MgO



D. CrO_2

Answer: D



15. The lattice site in a pure crystal cannot be occupied by :

A. molecule

B. ion

C. electron

D. atom

Answer: C



16. graphite cannot be classifed as

A. conducting solid

B. network solid

C. Covalent solid

D. ionic solid

Answer: D

Watch Video Solution

17. Cations are present in the interstitial sites in

A. Frenkel defect

B. Schottky defect

C. Vacancy defect

D. metal deficiency defect

Answer: A

.

Watch Video Solution

18. Schottky defect is observed in crystals when

A. some cations move from their lattice site

to intersititial sites

B. equal number of cations and anions are

missing form the lattice

C. some lattice sites are occupied by

electrons

D. some impurity is present in the lattice

Answer: B

Watch Video Solution

19. which of the following is true about the change the charge acquired by p- type semiconductors ?

A. Positive

B. Neutral

C. Neagative

D. Depends on conentraton of p impurity

Answer: B

Watch Video Solution

20. to get a n- type semiconductor from silicon

, it should be doped with a sustance with valency............

A. 2

B. 1

C. 3

D. 5

Answer: D



21. The total of tetrahedral voids in the face

centred unit cell is

A. 6

B. 8

C. 10

D. 12

Answer: B

Watch Video Solution

22. which of the following point defects are

shoen by AgBr (s) crystals ?

(a) Schottky defect

(b) Frenkel defect

(c) metal ecxess defect

(d) Metal deficiency defect

A. 1 and 2

B. 3 and 4

C. 1and 3

D. 2 and 4





23. In which pair most efficient packing is present?

A. Hcp and bcc

B. hcp and ccp

C. bcc and ccp

D. bcc and simple cubic cell





24. Percentage of free space in cubic in a bodycentred cubic unit cell is .

- A. 74
- B. 68
- C. 32

D. 26

Answer: C



25. which of the following statemets is not true about the hexagonal close packing ?

A. the coordination number is 12

B. it has 74 % packing efficiency

C. Tetrahedral voids of the second layer are

covered by the sphere of the third layer

D. in this arrangment spheres of the fouth

layer are exactly alingened with those of

the first layer

Answer: D

Watch Video Solution

26. in which of the following strutures corrding number for cations and anions in the packed structure will be same ?

A. Cl^- ions form fcc lattice and Na^+ ions occupy all octahedral voids of the unit cell B. Ca^{2+} ions form fcc lattice and F^{-} ions occupy all the eight tetrahedral voids of the unit cell C. O^{2-} ions form fcc lattice and Na^+ ions occupy all the eight tetrahedral voids of the unit cell

D. S^{2-} ions form fcc lattice and Zn^{2+} ions

go into go into alternate tetrahedral

voids of the unit cell

Answer: A

Watch Video Solution

27. What is the coordination number in a square close packed structures in two dimensions?

A. 2

B. 3

C. 4

D. 6

Answer: C

Watch Video Solution

28. which kind of defects are introduced by doping ?

- A. Dislocation defect
- B. Schottky defect
- C. Frenkel defect
- D. Electronic defect

Answer: D



29. silicon doped with electron rich impurity

forms

A. p- type semiconductor

B. n- type semicondutor

C. intrinsic semiconductor

D. insulation

Answer: B



30. which of the following statements is not

true ?
A. Paramagnetic substances are weakly							
attracted by magnetic field							
B. Ferromagnetic substance cannot be							
magnetised permanently							
C. the domains in antiferromagnetic							
substance are oppositely oriented with							
respect to each other							
D. Paring of electrons cancels their							
magnetic moment in the diamagnetic							
substances							

Answer: B



31. which of the following is not true about the ionic solids ?

(a)Bigger ions form the close packed structure

(b)smaller ions either occupy the tetrahedral

or the octahedral voids depending upon their

size

(c)Occupation of all voids is not necessary

(d)the fraction of octahedral or tetrahedral

voids occupied depends upon the radii of the

ions occupying the voids

A. Bigger ions form the close packed structure

B. smaller ions either occupy the

tetrahedral or the octahedral voids

depending upon their size

C. Occupation of all voids is not necessary

D. the fraction of octahedral or tetrahedral

voids occupied depends upon the radii

of the ions occupying the voids

Answer: D

Watch Video Solution

32. A ferromagnetic substance becomes a permanent magnet when it is placed in a magnetic field because:

A. all the domains get oriented in the

direction of magnetic field

B. all the domains get oriented in the direction opposite to the direaction o magnetic field C. Domains get ori ented randomy D. Domains are not affected by magnetic field

Answer: A

33. the correct order of the packing effeciency

in different types of unit cells is

A. fccltBcclt simple cubic

B. fccgt bcc gt simple cubic

C. fcclt bcc? Simple cubic

D. bcclt fccgt simple cubic

Answer: B

34. which of the follwing defects is also known

as dislocation defect ?

A. Frenkel defect

B. Schottky defect

C. Non-stoichiometric defect

D. simple inter stitial defect

Answer: A

35. in the cubic packing , the unit cell has

A. 4 tetrahedral voids each of which is

shared by four adjacent unit cells

- B. 4 tetrahedral voids within the unit cell
- C.8 tetrahedral voids each of which is

shared by four adjacent unit cells

D. 8 tetrahedral voids within the unit cells

Answer: D



A.
$$2\sqrt{2r}, \frac{4r}{\sqrt{3}}, 2r$$

B. $\frac{4r}{\sqrt{3}}, 2\sqrt{2r}, 2r$
C. $2r, 2\sqrt{2r}, \frac{4r}{\sqrt{3}}$
D. $2r, \frac{4r}{\sqrt{3}}, 2\sqrt{2r}$

Answer: A

37. which of the following repesents correct order of conductivity in solids ?

A.
$$k_{metals} > > k_{insulators} < k_{semiconductors}$$

B. $k_{metals} < < k_{insulators} < k_{semiconductors}$
C.
 $k_{metals} \cdot , k_{semiconductors} > k_{insulations} = zero$
D.
 $k_{metals} \cdot , k_{semiconductors} > k_{insulations} \neq zero$

Answer: A



38. Which of the following is not true about the voids formed in 3 dimensional hexagonal close packed structure?

A. A tetrahedral void is formed when a

sphere of the second layer is present

above triangular void in the first layer

B. all the triangular voids in the first layer

C. tetrahedral voids are formed when the triangular voids in the second layer lie above the first layer and the triangular shpes of these voids do not overlap D. Octahedral voids are formed when the triangular voids in the second layer exctly overlap with similar voids in the first layer

Answer: C,D

View Text Solution

39. the value of magnetic moment is zero in the case of antiferromagnetic substaence because the domains

A. get oriented in the direction of the applied magnetic fleidB. get oriented opposite to the direction to the direction of the appiled magnetic

fleld

C. are oppositely oriented with respect to each other without the application of magnetic field D. cancel out each other 's magnetic

moment

Answer: C,D

40. which of the following statement are not true ?

(a) Vacancy defect results in a decrease in the

density of the substance

(b)interstitial defects results in an increase in

the density of the substance

(c)impurity defect has no effect on the density

of the substance

(d)Frenkel defect results results in an increase

in the density of the substance

A. Vacancy defect results in a decrease in

the density of the substance

B. interstitial defects results in an increase

in the density of the substance

C. impurity defect has no effect on the

density of the substance

D. Frenkel defect results results I n an

increase in the density of the substance

Answer: C,D

41. which of the following statements are true about metals? (a) Valence band overlaps with conduction band (b)the gap between valence band and conduction band is negligible (c) the gap[between valence band and conduction band cannot be determined (d) Valence band may remain partially filled

A. Valence band overlaps with conduction band B. the gap between valence band and conduction band is negligible C. the gap[between valence band and conduction band cannot be determinted D. Valence band may ramain partially filled

Answer: A,B,D

42. under the influence of electric field , which of the following statement is true about the movement of electrons and holes in p- type semiconducter ?

A. Electron will move towards the positively charged plate through electron holes B. Holes will appear to be moving towards the negatively chared plate C. both electrons and holes appear to move towards the positively charged

plate

D. Movement of elecrons Is not reated to

the movement of holes

Answer: A,B

Watch Video Solution

43. which of the following statements are true

about semiconductor ?

(a)silicon doped with electron rich impurity is

a p-type semiconductor

(b)Silicon	doped	with	an	electrons	rich			
impurity is an n-type semiconductor								
(c)Delocalised		electrons		increase	the			
conductivity of doped silicon								
(d)An	electron	vacar	тсу	increase	the			
conductivity of n- type semiconductor								
A. silicon doped with electron rich impurity								
is a p-type semiconductor								
B. Silio	con dope	ed with	n an	electrons	rich			
impuriy is an n-type semipucoter								

C. Delocalised electrons increase the conductivity of doped silicon

D. An electron vacancy incease the

conductivity of n- type semiconductor

Answer: B,C

Watch Video Solution

44. An excess of potassium ions makes KCL crystals appear violet or lilac in colour since

A. some of the anionic sites are occupied

by an unpaired electron

B. some of the anionic sites are occupied

by an pair of electrons

C. there are vacancies at some anionic sites

D.F - centres are created which impart

colour to the crystals

Answer: A,D

45. the number of tetrahedral voids per unit

cell in NaCl crystal is

A. 4

B. 8

C. twice the number of octahedral voids

D. Four times the number of octahedral

voids

Answer: B,C

46. Amorphous solids can also be callled

A. pseudo solids

B. true solids

C. super cooled liquids

D. super cooled solids

Answer: A,C

47. A perfect crystal of silicon (fig) is deped with some elements as given in the options , which of these options shows n- type semicondutors ?







Answer: A,C

48. which of the following statements are correct? substance (a)Ferrimagnetic lose ferrimagnetism on heating and become paramagnetic (b)Ferrimagnetic substance do not lose ferrimagnetism on heating and Remain ferromagnetic (c)Antiferromgnetic substance have domain structures similar to ferromagnetic substance and their magnetic moment are not cancelled by each other

(d)Antiferromagnetic substance have domain structures similar to ferromagnetic substance and their magnetic moment are not cancelled by each other

A. Ferrimagnetic substance lose ferrimagnetism on heating and become paramagetic B. Ferrimagnetic substance do not lose ferrimagnetism on heating and Reamain ferrmagnetic

C. Antiferromgnetic subst			ance	have			
domain	structur	es s	imolar	to			
ferromagne	etic sub	stance	and	their			
magngnetic moment are not cancelled							
by eash other							
D. in ferroma	agnetic s	substan	ce,a	ll the			
domains get oriented in the directon of							
magnetic field and ramain as such even							
after remov	ving magi	netic fie	ld				

Answer: A,D



49. which of the following feastures are not shown by quartz glass ?

A. this is a crystalline solid

B. Refractive index is same in all the

directions

C. this has define heat of fusion

D. this is also called super cooled liquid

Answer: A,C



50. which of the following cannot regarded as

molecular solid ?

A. AiC (silicon carbide)

B. AIN

C. Diamond

D. I_2

Answer: A,B,D



51. in which of the following arrangement octahedral voids are formed ?

A. hcp

B. bcc

C. simple cubic

D. fcc

Answer: A,D



D. non-stoichometric defect

Answer: A,B



53. which of the following defects decrase the density decrease the density ?

A. interstitial defect

B. Vacancy defect

C. Frenkel defect

D. Schottky defect





Short Answer Type Questions

1. Why are liquids and gases categorised as

fluids?
2. Why are solids incompressible ?



3. Inspite of long range order in the arrangement of particles why are the crystals usually not perfect ?



5. why is FeO(s) not formed in stoichiometric

compostion ?

6. why does white ZnO(s) becomes yellow upon

heating ?

Watch Video Solution

7. why does the electrical conductivity of semiconductors increase with rise in temperature?

8. Explain why does conductivity of germainum

crystals increase on doping with galium ?

Watch Video Solution

9. A compound formed by two elements M and N. Element N forms ccp and atoms of M occupy 1/3rd of tetrahedral voids. What is the formula of th compound?

10. Under which situations can an amorphous

substance change to crystaline form?

Watch Video Solution

11. match the type of unit cell given column I

with the features iven in Column II.

	Column I	T	Column II
A.	Primitive cubic unit cell	1.	Each of the three perpendicular edges compulsorily have the different edge length <i>i.e.,</i> $a \neq b \neq c$
В.	Body centred cubic unit cell	2.	Number of atoms per unit cell is one
C.	Face centred cubic unit cell	3.	Each of the three perpendicular edges compulsorily have the same edge length <i>i.e.</i> , $a = b = c$
D.	End centred orthorhombic unit cell	4.	In addition to the contribution from the corner atoms the number of atoms present in a unit cell is one
		5.	In addition to the contribution from the corner atoms the number of atoms present in a unit cell is three



12. match the types of defect given in column I

with the statement given in column II.

	Column I		Column II
Α.	Impurity defect	1.	NaCl with anionic sites called F-centres
В.	Metal excess defect	2.	FeO with Fe ³⁺
С.	Metal deficiency defect	3.	NaCl with Sr ²⁺ and some cationic sites vacant



Watch Video Solution

13. match the items given in column I with the

items given in column II.

	Column I		Column II
A.	Mg in solid state	1.	p-type semiconductor
В.	MgCl ₂ in molten state	2.	n-type semiconductor
C.	Silicon with phosphorus	3.	Electrolytic conductors
D.	Germanium with boron	4.	Electronic conductors

14. Match the type of packing given in column I

with the iterms given in column II.

	Column I		Column II
А.	Square close packing in two dimensions	1.	Triangular voids
B .	Hexagonal close packing in two dimensions	2.	Pattern of spheres is repeated in every fourth layer
С.	Hexagonal close packing in three dimensions	3.	Coordination number = 4
D.	Cubic close packing in three dimensions	4.	Pattern of sphere is repeated in alternate layers

Watch Video Solution

15. Assertion :- (A) The total number of atoms

present in a simple cubic unit cell is one.

Reason :-(R) Simple cubic cell has atoms at its corners, each of which is shared between eight adjacent unit cells.

A. Assertion and reason both are correct statements and Reason is correct explantion for Assertion .

B. Asserton and Reason both are correct statement but Reason is not correct

explanation for assertion .

C. Assertion is correct statement but

reason is worng statement.

D. Assertion is Wrong statement but

Reason is correct statement.

Answer: A

Watch Video Solution

16. Assertion :- (A) Graphite is good conductor

of electricity however diamond belongs to the

category of insulators .

Rason (R) Grapite is soft in anture on the hand diamond is very hard and brittle.

A. Assertion and reason both are correct

statements and Reason is correct

explantion for Assertion .

B. Asserton and Reason both are correct

statement but Reason is not correct

explanation for assertion .

C. Assertion is correct statement but

reason is worng statement.

Reason is correct statement.

Answer: B



17. Assertion :- (A) total number of octahedral voids present in unit cell of cubic close of each packing including the one that is present at the body centre . Is four .

Reason :- (R) Besides the body centre there is

one octahedral void present at the centre of each of the six faces of the unit cell and each of which is shared between two adjeccent units cells.

A Assertion and reason both are correct statements and Reason is correct explantion for Assertion. B. Asserton and Reason both are correct statement but Reason is not correct explanation for assertion.

C. Assertion is correct statement but

reason is worng statement.

D. Assertion is Wrong statement but

Reason is correct statement.

Answer: C

Watch Video Solution

18. Assertion :- (A) the paking efficiency is maximum for the fcc struture .

Reason :- (R) the coordination number is 2 in

fcc structures.

A. Assertion and reason both are correct

statements and Reason is correct

explantion for Assertion .

B. Asserton and Reason both are correct

statement but Reason is not correct

explanation for assertion.

C. Assertion is correct statement but

reason is worng statement.

Reason is correct statement .

Answer: B

Watch Video Solution

19. Assertion :-(A) semiconductors are solids with conductivites in the intermediate range from $10^{-6} - 10^4 ohm^{-1}m^{-1}$ Reason :-(R) internmediate conductivity in semiconductor Is due to partially filled valence band .

A. Assertion and reason both are correct

statements and Reason is correct

explantion for Assertion .

B. Asserton and Reason both are correct

statement but Reason is not correct

explanation for assertion .

C. Assertion is correct statement but

reason is worng statement.

D. Assertion is Wrong statement but

Reason is correct statement.

Answer: C

Watch Video Solution

Matching The Columns

1. match the defects given in column I with the

statements in given Column I.

	Column I		Column II
A.	Simple vacancy defect	1.	Shown by non-ionic solids and increases density of the solid
В.	Simple interstitial defect	2.	Shown by ionic solids and decreases density of the solid
C.	Frenkel defect	3.	Shown by non-ionic solids and density of the solid decreases
D.	Schottky defect	4.	Shown by ionic solids and density of the solid remains the same



Long Answer Type Questions

1. With the help of a labelled diagram show that there are four octahedral voids per unit cell in cubic close packed structure .



2. Show that in a cubic close packed structure eight tetrahedral voids are present per unit cell.



3. How does the doping increase the

conductivity of semiconductor ?

4. The composition of a sample of wustite is $Fe_{0.93}O_{1.00}$. What percentage of iron is present in the form of Fe(III)?